STH275N8F7-2AG, STH275N8F7-6AG

Automotive-grade N-channel 80 V, 0.0017 Ω typ., 180 A, STripFET™ F7 Power MOSFETs in H²PAK-2 and H²PAK-6

Datasheet – production data

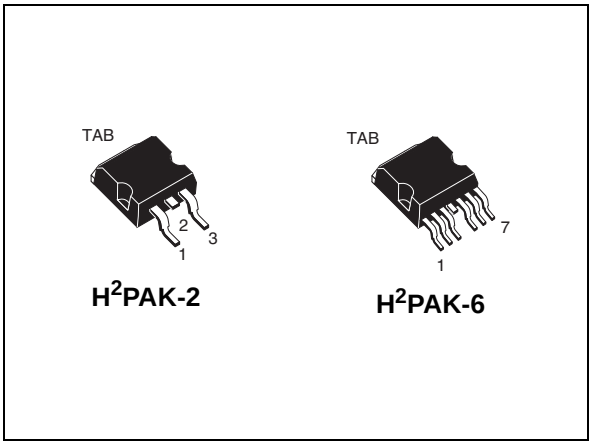
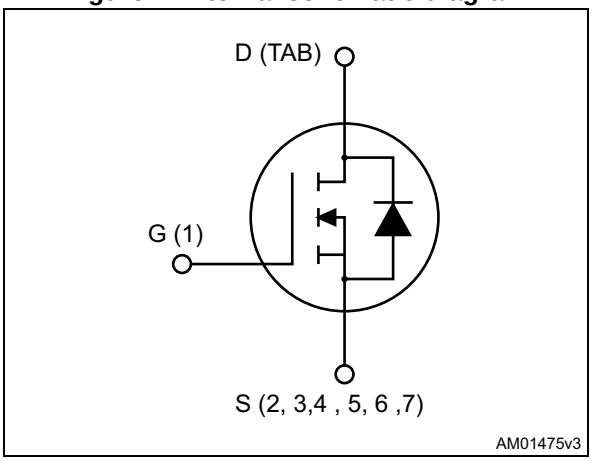


Figure 1. Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STH275N8F7-2AG	80 V	0.0021 Ω	180 A
STH275N8F7-6AG			

- Designed for automotive applications and AEC-Q101 qualified
- Among the lowest $R_{DS(on)}$ on the market
- Excellent figure of merit (FoM)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

These N-channel Power MOSFETs utilize STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1. Device summary

Order code	Marking	Package	Packaging
STH275N8F7-2AG	275N8F7	H²PAK-2	Tape and reel
STH275N8F7-6AG		H²PAK-6	

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	± 20	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	180	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	180	A
I_{DM} (2)	Drain current (pulsed)	720	A
P_{TOT} (3)	Total dissipation at T_C = 25 °C	315	W
E_{AS} (4)	Single pulse avalanche energy	1.16	J
T_J	Operating junction temperature range	-55 to 175	°C
T_{stg}	Storage temperature range		°C

1. Limited by package
2. Pulse width limited by safe operating area
3. This value is rated according to $R_{thj\text{-}c}$
4. Starting T_j = 25°C, I_d = 65 A, V_{dd} = 50 V

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	0.48	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	35	°C/W

1. When mounted on FR-4 board of 1 inch^2, 2oz Cu

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS}= 0 V, I_D = 1 mA	80			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 80 V			1	µA
		V_{GS} = 0 V, V_{DS} = 80 V, T_C=125 °C (1)			100	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = +20 V			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250 µA	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on- resistance	V_{GS}= 10 V, I_D= 90 A		0.0017	0.0021	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS}=0 V, V_{DS} =50 V, f=1 MHz	-	13600	-	pF
C_{oss}	Output capacitance		-	2050	-	pF
C_{rss}	Reverse transfer capacitance		-	236	-	pF
Q_g	Total gate charge	V_{DD}=40 V, I_D = 180 A V_{GS} =10 V *Figure 14*	-	193	-	nC
Q_{gs}	Gate-source charge		-	96	-	nC
Q_{gd}	Gate-drain charge		-	46	-	nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD}=40 V, I_D= 90 A, R_G=4.7 Ω, V_{GS}= 10 V *Figure 13*	-	56	-	ns
t_r	Rise time		-	180	-	ns
$t_{d(off)}$	Turn-off delay time		-	98	-	ns
t_f	Fall time		-	42	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		180	A
I_{SDM}(1)	Source-drain current (pulsed)		-		720	A
V_{SD}(2)	Forward on voltage	V_{GS}=0 V, I_{SD} = 90 A	-		1.2	V
t_{rr}	Reverse recovery time	I_{SD} = 180 A, di/dt = 100 A/µs, V_{DD}=64 V, T_j=150 °C	-	78		ns
Q_{rr}	Reverse recovery charge		-	182		nC
I_{RRM}	Reverse recovery current		-	4.7		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

3 Electrical characteristics (curves)

Figure 2. Safe operating area

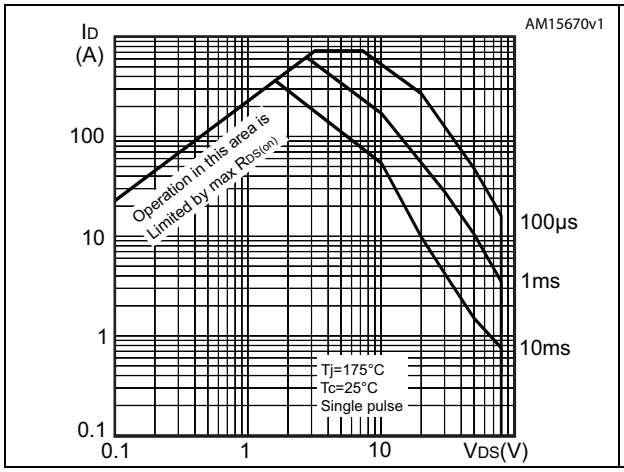


Figure 3. Thermal impedance

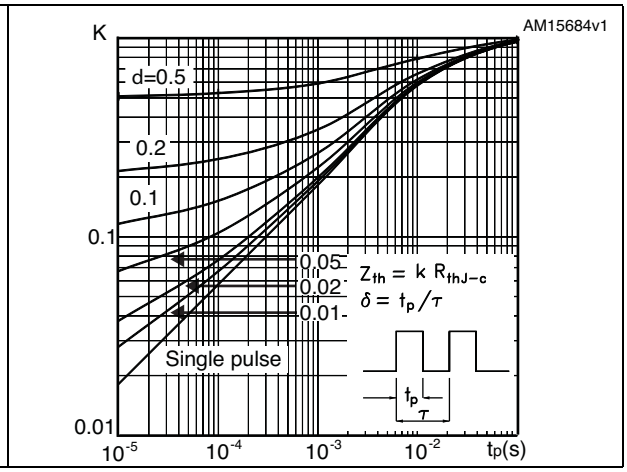


Figure 4. Gate charge vs gate-source voltage

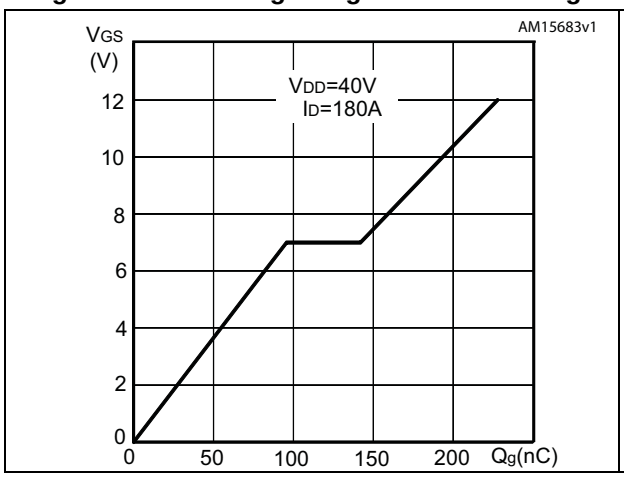


Figure 5. Output characteristics

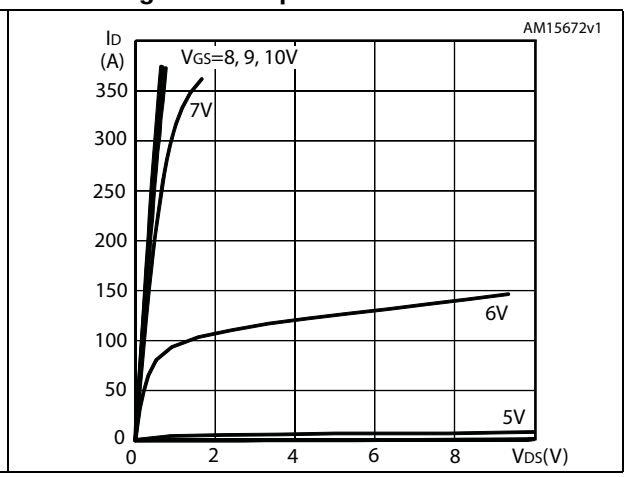


Figure 6. Transfer characteristics

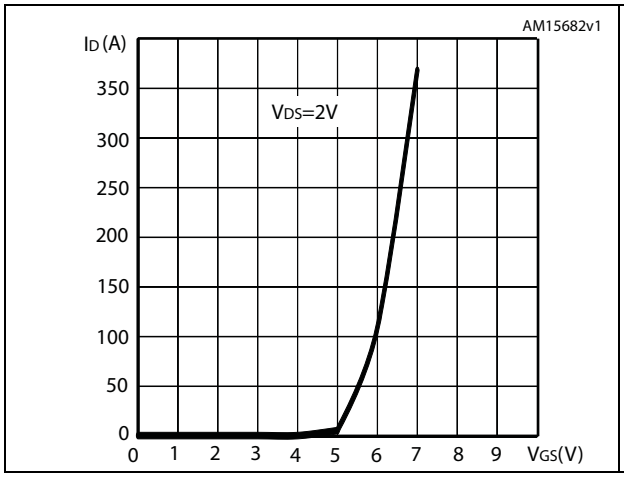


Figure 7. Normalized $V_{(BR)DSS}$ vs temperature

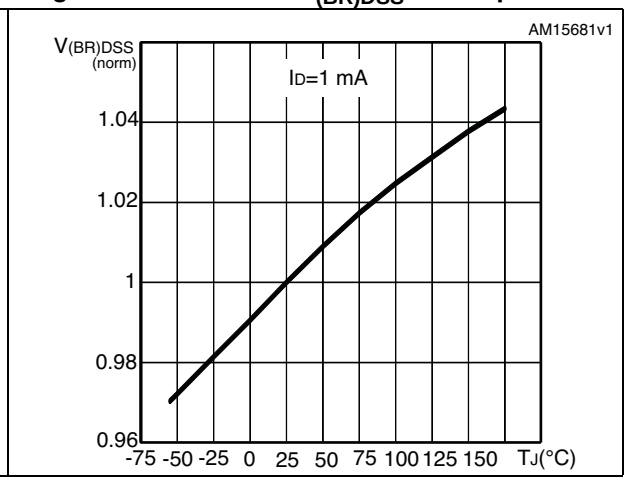


Figure 8. Static drain-source on-resistance

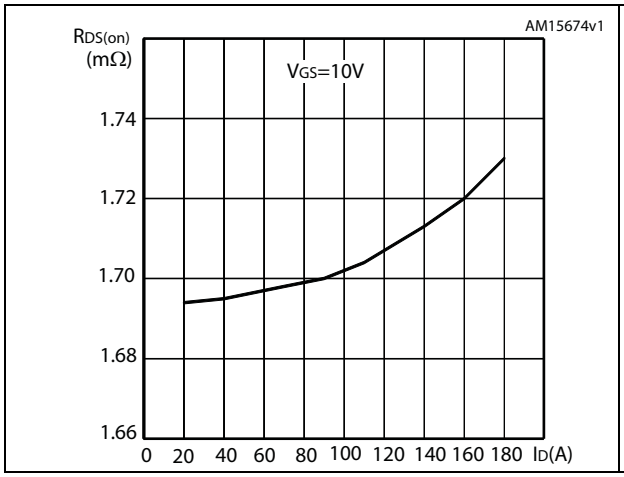


Figure 9. Capacitance variations

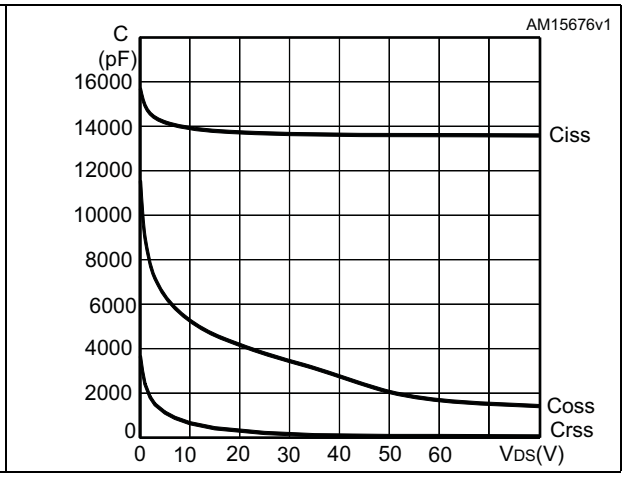


Figure 10. Source-drain diode forward characteristics

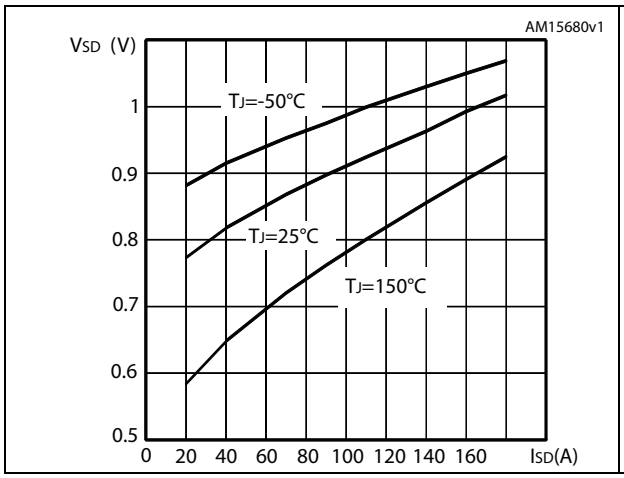


Figure 11. Normalized gate threshold voltage vs temperature

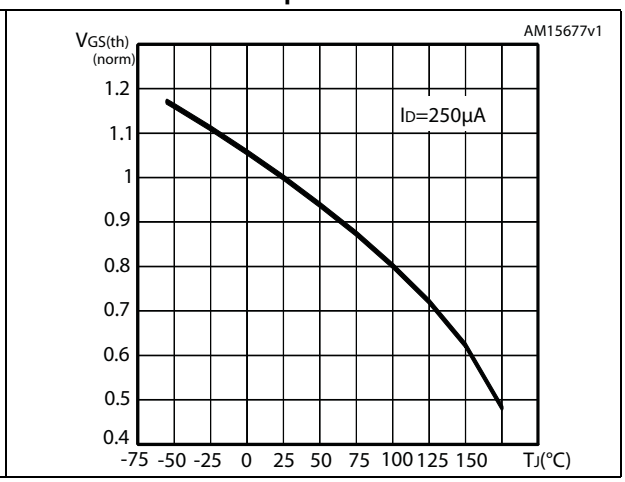
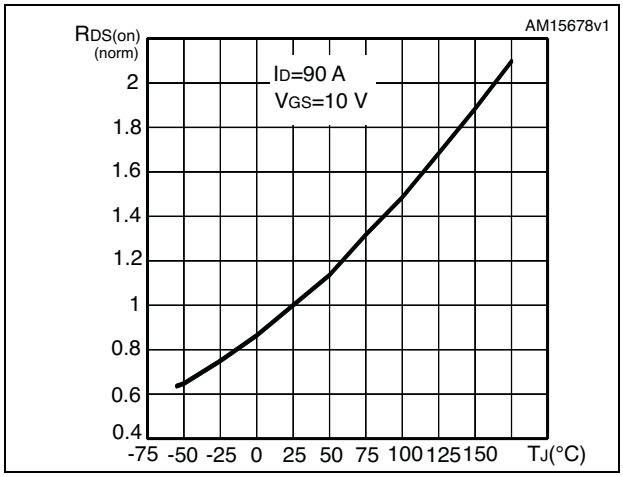


Figure 12. Normalized on-resistance vs temperature



4 Test circuits

Figure 13. Switching times test circuit for resistive load

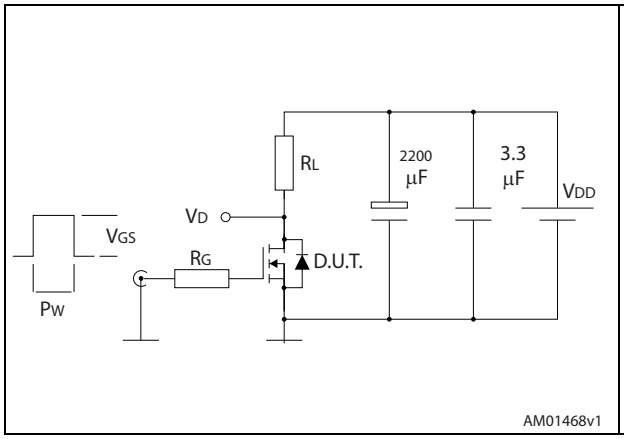


Figure 14. Gate charge test circuit

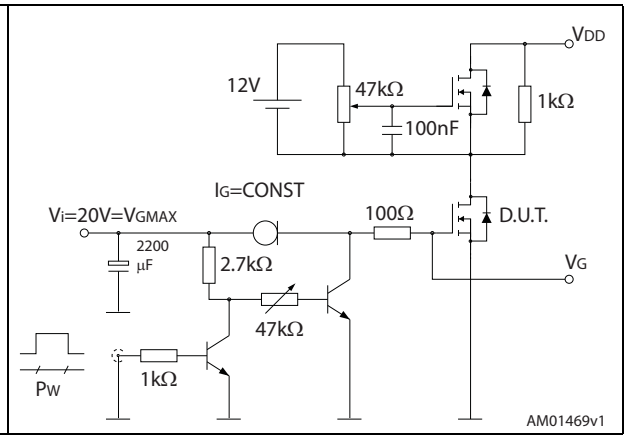


Figure 15. Test circuit for inductive load switching and diode recovery times

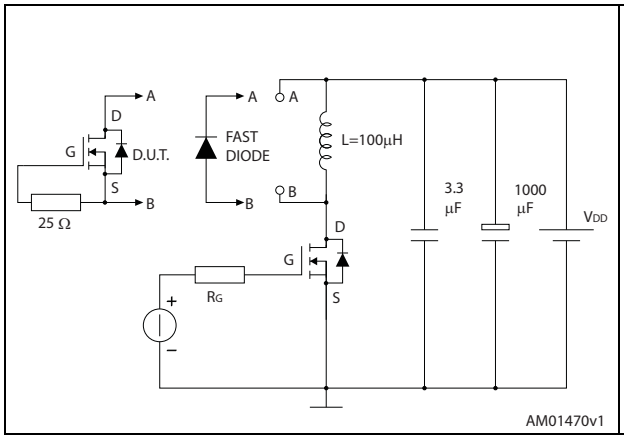


Figure 16. Unclamped inductive load test circuit

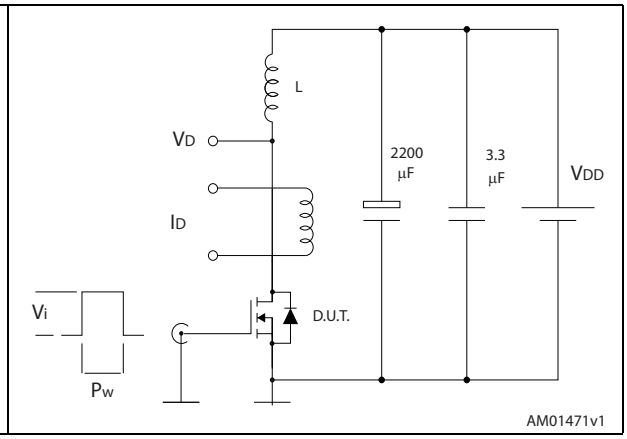


Figure 17. Unclamped inductive waveform

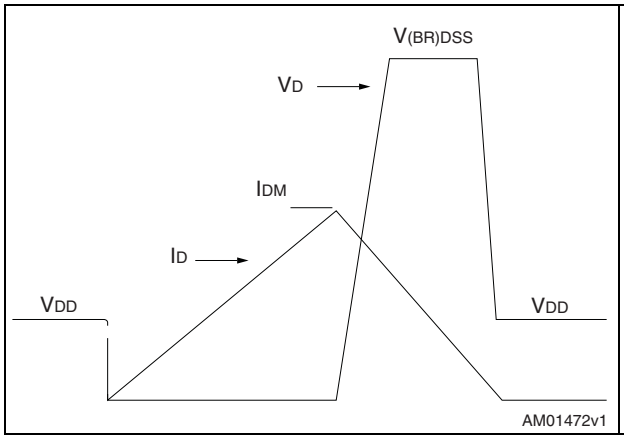
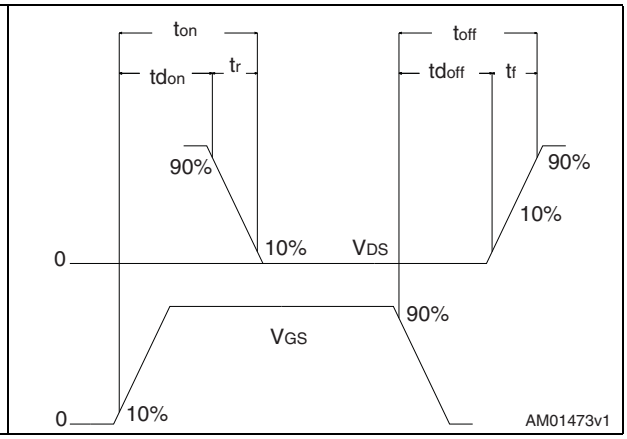


Figure 18. Switching time waveform



5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

5.1 H²PAK-2, STH275N8F7-2AG

Figure 19. H²PAK-2 drawing

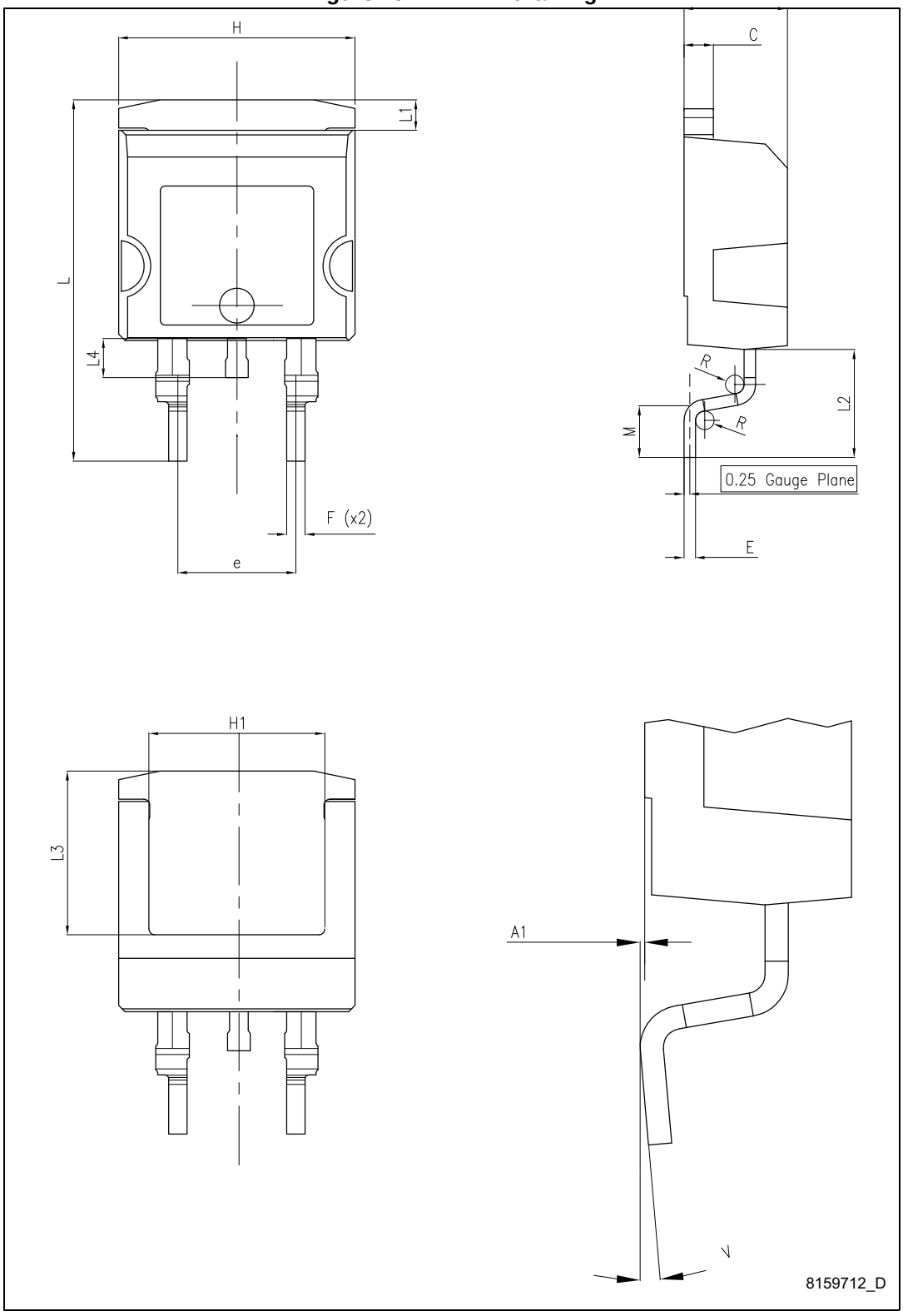
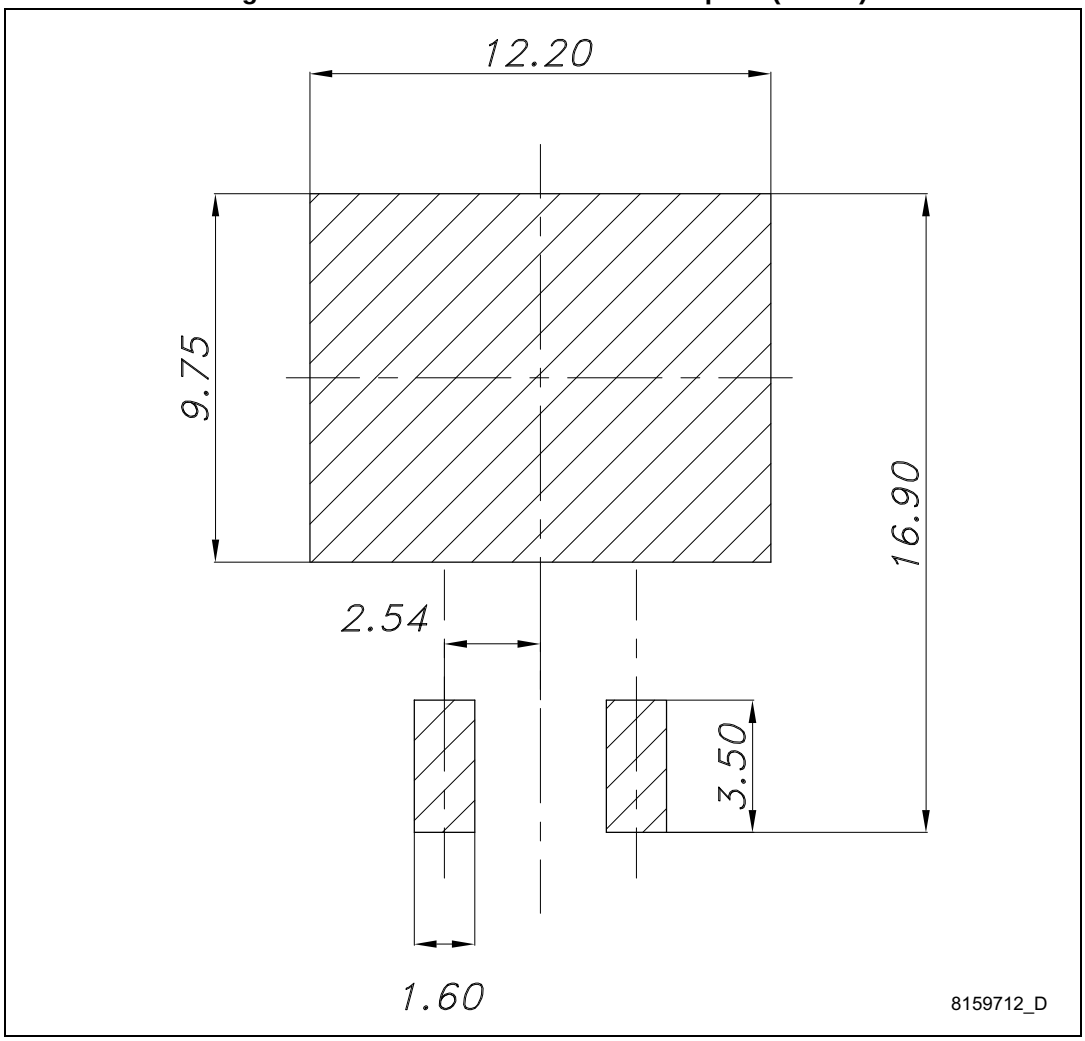


Table 8. H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 20. H²PAK-2 recommended footprint (in mm)



5.2 H²PAK-6, STH275N8F7-6AG

Figure 21. H²PAK-6 drawing

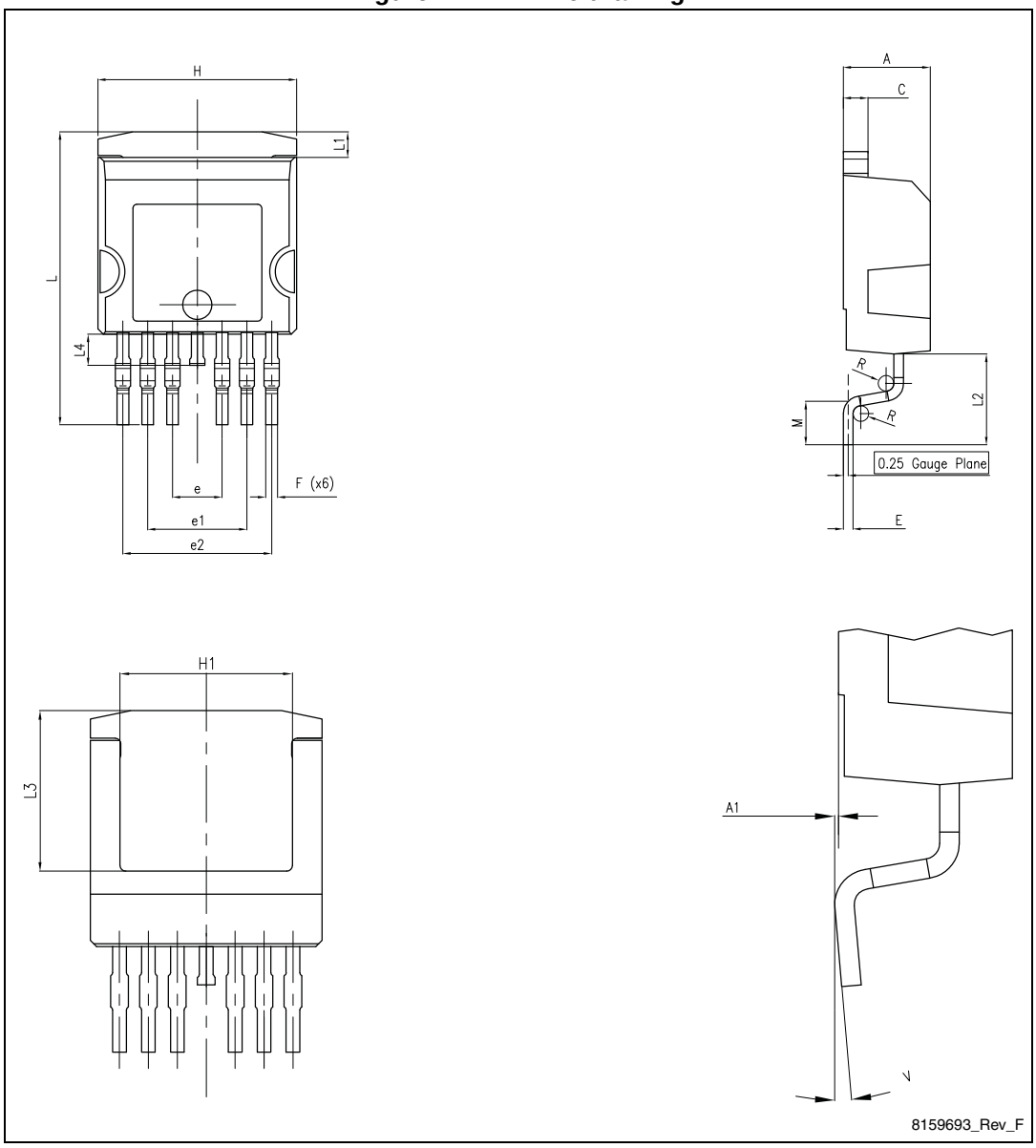
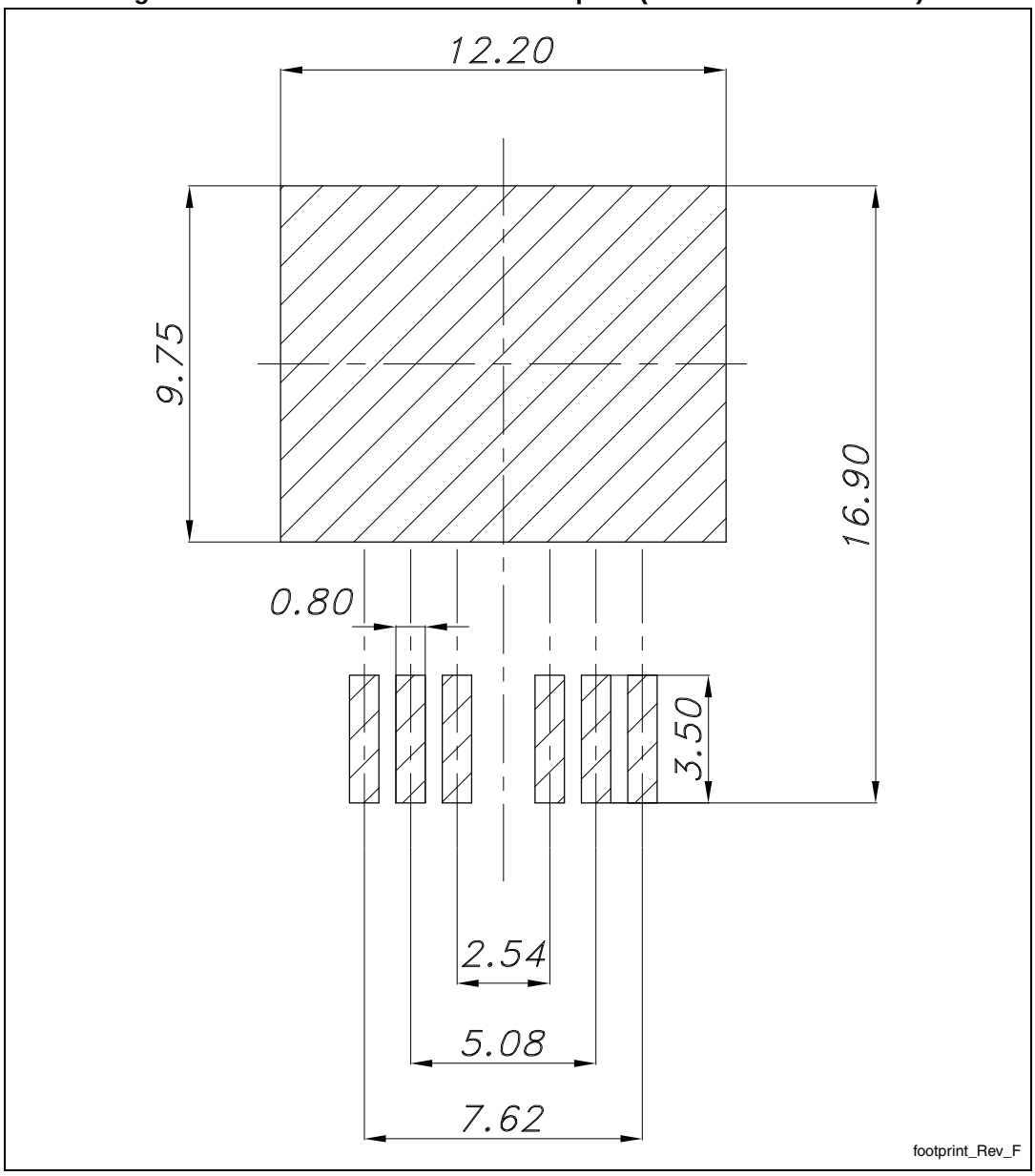


Table 9. H²PAK-6 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.80
A1	0.03		0.20
C	1.17		1.37
e	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00	-	10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 22. H²PAK-6 recommended footprint (dimensions are in mm)



6 Packaging information

Figure 23. Tape

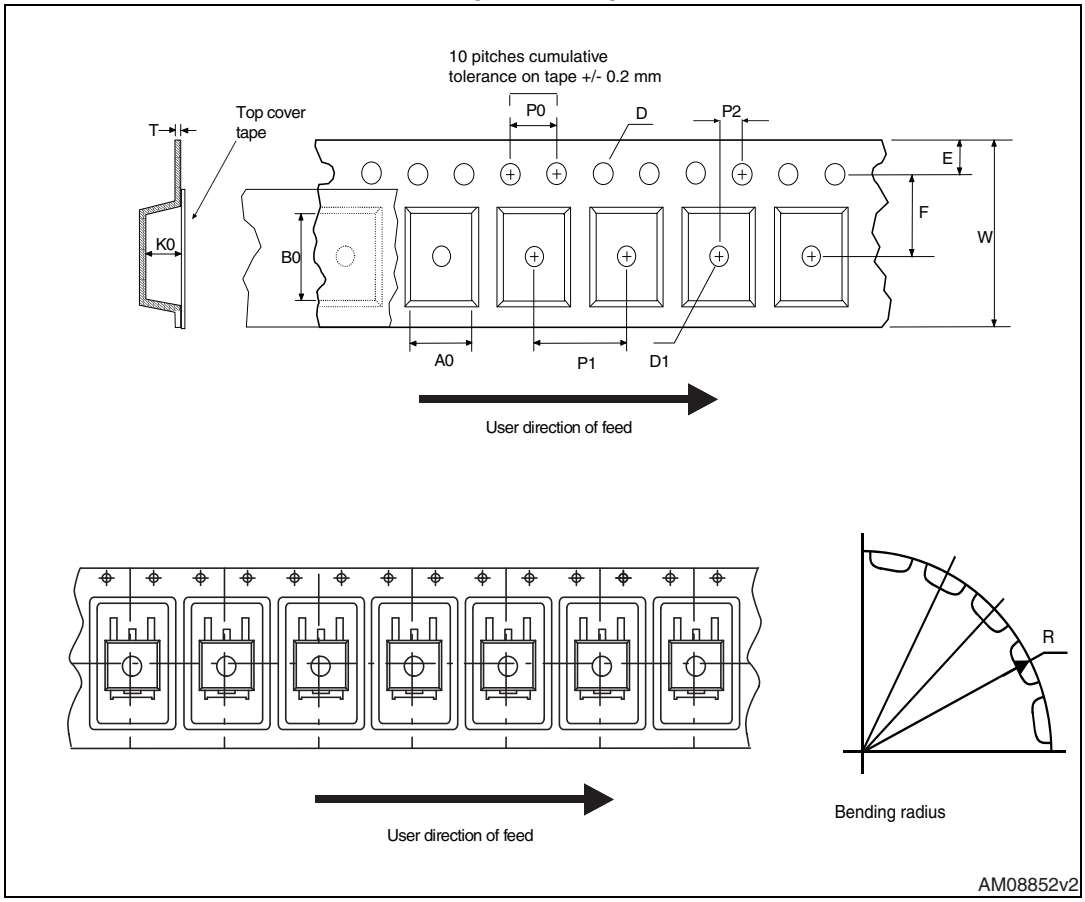


Figure 24. Reel

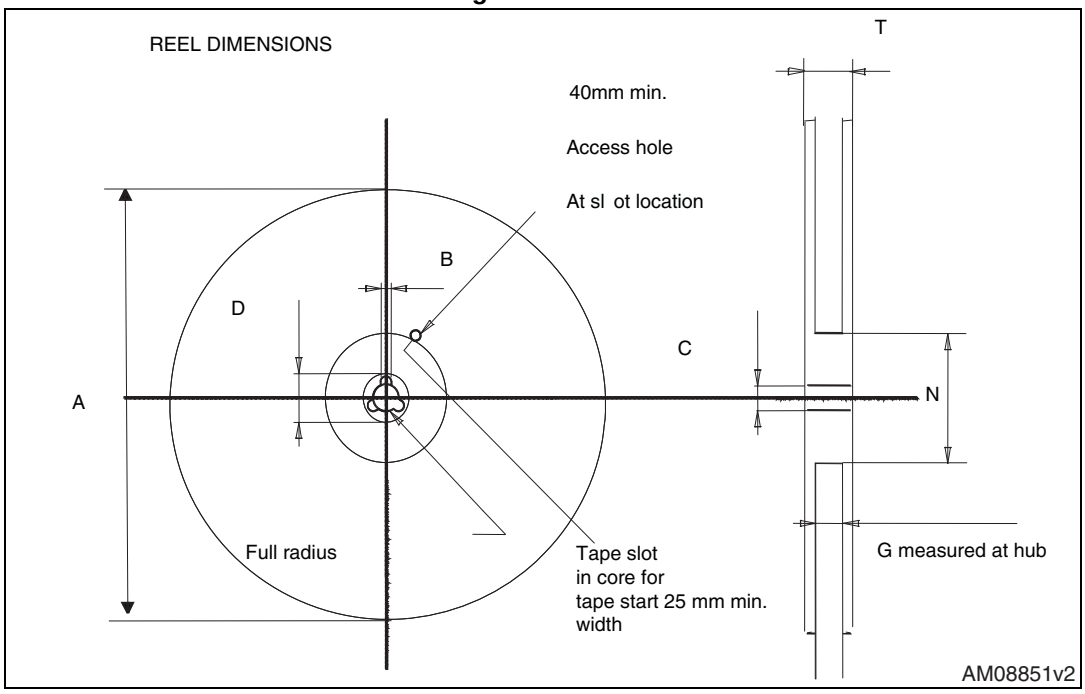


Table 10. Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

7 Revision history

Table 11. Document revision history

Date	Revision	Changes
27-Nov-2014	1	First release.
05-Mar-2015	2	Document status promoted from preliminary to production data. Updated title and feature in cover page.
10-Mar-2016	3	Updated *Table 4*. Minor text changes.

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